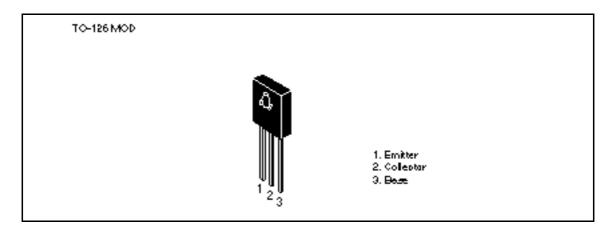
Silicon PNP Epitaxial

HITACHI

Application

Low frequency power amplifier complementary pair with 2SD669/A

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| | | Ratings | | | |
|------------------------------|----------------------|-------------|-------------|------|--|
| Item | Symbol | 2SB649 | 2SB649A | Unit | |
| Collector to base voltage | V _{CBO} | -180 | -180 | V | |
| Collector to emitter voltage | V_{CEO} | -120 | -160 | V | |
| Emitter to base voltage | V_{EBO} | - 5 | - 5 | V | |
| Collector current | I _c | -1.5 | −1.5 | A | |
| Collector peak current | I _{C(peak)} | -3 | -3 | A | |
| Collector power dissipation | P _c | 1 | 1 | W | |
| | P _c *1 | 20 | 20 | W | |
| Junction temperature | Tj | 150 | 150 | °C | |
| Storage temperature | Tstg | -55 to +150 | -55 to +150 | °C | |

Note: 1. Value at $T_c = 25^{\circ}C$

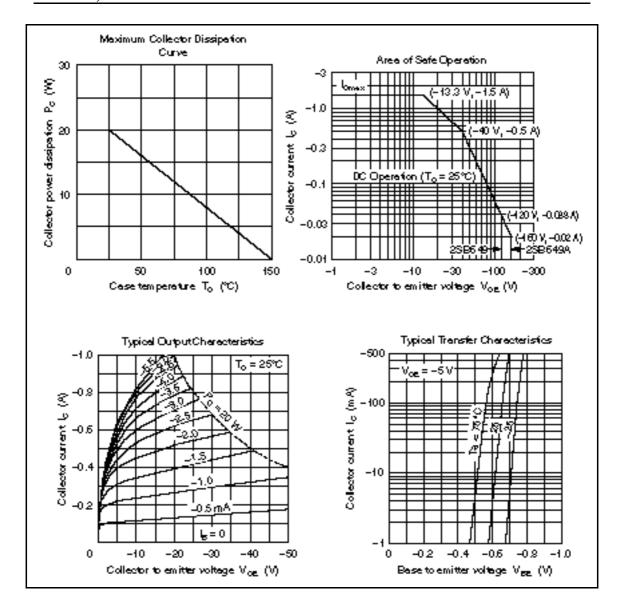
Electrical Characteristics ($Ta = 25^{\circ}C$)

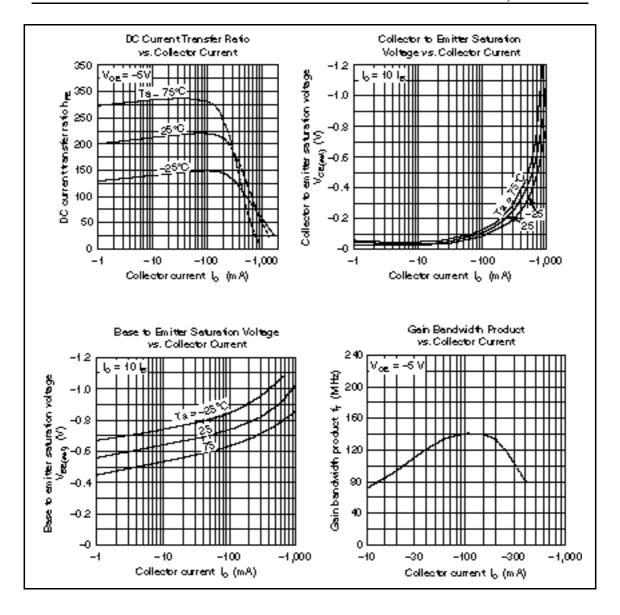
| | | 2SB6 | 49 | | 2SB649A | | | | |
|---|----------------------|------------|-----|------|------------|-----|------|------|--|
| Item | Symbol | Min | Тур | Max | Min | Тур | Max | Unit | Test conditions |
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | -180 | _ | _ | -180 | _ | _ | V | $I_{\rm C} = -1 \text{ mA}, I_{\rm E} = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -120 | _ | _ | -160 | _ | _ | V | $I_{\rm C} = -10 \text{ mA}, R_{\rm BE} =$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | – 5 | _ | _ | - 5 | _ | _ | V | $I_{E} = -1 \text{ mA}, I_{C} = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | -10 | _ | _ | -10 | μΑ | $V_{CB} = -160 \text{ V}, I_{E} = 0$ |
| DC current transfer ratio | h _{FE1} *1 | 60 | _ | 320 | 60 | _ | 200 | | $V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA}$ |
| | h _{FE2} | 30 | _ | _ | 30 | _ | _ | | $V_{CE} = -5 \text{ V},$ $I_{C} = -500 \text{ mA}^{*2}$ |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | _ | _ | -1 | _ | _ | -1 | V | $I_{\rm C} = -500 \text{ mA},$ $I_{\rm B} = -50 \text{ mA}$ |
| Base to emitter voltage | V_{BE} | _ | _ | -1.5 | _ | _ | -1.5 | V | $V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA}$ |
| Gain bandwidth product | f _T | _ | 140 | _ | _ | 140 | _ | MHz | $V_{CE} = -5 \text{ V},$ $I_{C} = -150 \text{ mA}$ |
| Collector output capacitance | Cob | _ | 27 | _ | _ | 27 | _ | pF | $V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz |

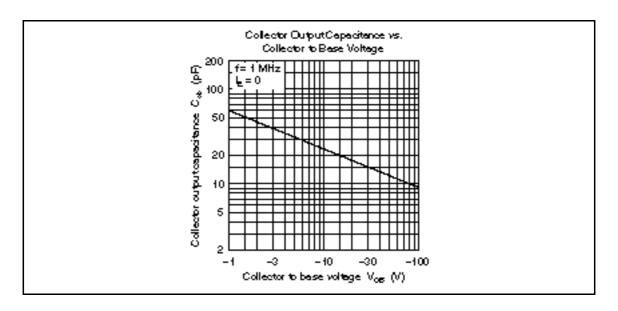
Notes: 1. The 2SB649 and 2SB649A are grouped by h_{FE1} as follows.

2. Pulse test

| | В | С | D |
|---------|-----------|------------|------------|
| 2SB649 | 60 to 120 | 100 to 200 | 160 to 320 |
| 2SB649A | 60 to 120 | 100 to 200 | _ |







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